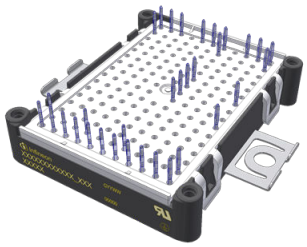
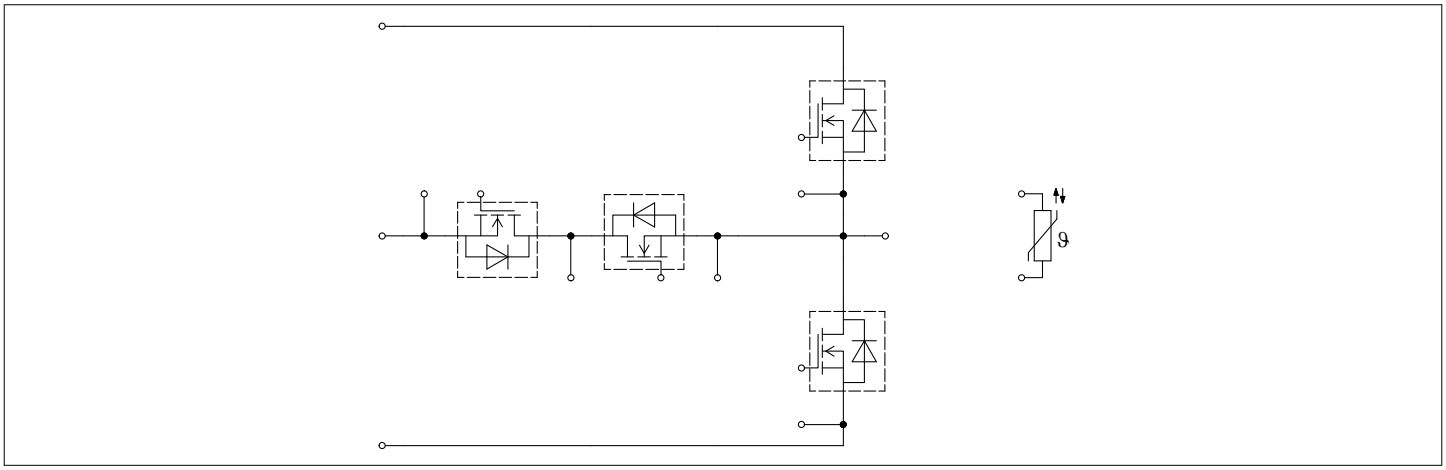
Preliminary datasheet
EasyPACK™ module with CoolSiC™ Trench MOSFET and PressFIT / pre-applied thermal interface material / NTC



Features
- Electrical features
  - V_{DSS} = 1200 V
  - I_{DN} = 75 A / I_{DRM} = 150 A
  - Low inductive design
  - Low switching losses
  - High current density
  - Suitable Infineon gate drivers can be found under https://www.infineon.com/gdfinder
- Mechanical features
  - PressFIT contact technology
  - Integrated NTC temperature sensor
  - Rugged mounting due to integrated mounting clamps
  - Package with CTI > 600
  - High current pin

Potential applications
- High-frequency switching application
- DC/DC converter
- DC charger for EV

Product validation
- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 1 min	3.0	kV
Isolation test voltage NTC	$V_{ISOL(NTC)}$	RMS, f = 50 Hz, *t* = 1 min	3.0	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Comparative tracking index	*CTI*		> 600	
Relative thermal index (electrical)	*RTI*	frame	130	°C
		lid	130	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			19		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_H = 25 °C, per switch		2.6		mΩ
Storage temperature	T_{stg}		-40		130	°C
Maximum baseplate operation temperature	T_{BPmax}				150	°C
Mounting force per clamp	*F*		40		80	N
Weight	*G*			38		g

***Note**: The current under continuous operation is limited to 50 A rms per connector pin.*
Storage and shipment of modules with TIM => see AN 2012-07

2 MOSFET, T1 / T2

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	1200	V
Implemented drain current	I_{DN}			75	A
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_H = 25 °C	95	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		150	A
Gate-source voltage, max. transient voltage	V_{GS}	*D* < 0.01		-10/25	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 4 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 75 A	V_{GS} = 18 V, T_{vj} = 25 °C		8.3		mΩ
			V_{GS} = 18 V, T_{vj} = 125 °C		13		
			V_{GS} = 18 V, T_{vj} = 175 °C		16.8		
			V_{GS} = 15 V, T_{vj} = 25 °C		10		
Gate threshold voltage	$V_{GS(th)}$	I_D = 33 mA, V_{DS} = V_{GS}, T_{vj} = 25 °C, (tested after 1ms pulse at V_{GS} = +20 V), T_{vj} = 25 °C		3.45	4.3	5.15	V
Total gate charge	Q_G	V_{DD} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			0.237		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			3.5		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		7.21		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.293		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.02		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			121		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = -3 V	T_{vj} = 25 °C		0.3	296	µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = 20 V			400	nA
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 75 A, R_{Gon} = 10 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V, t_{dead} = 1000 ns, 0.1 V_{GS} to 0.1 I_D	T_{vj} = 25 °C		50.4		ns
			T_{vj} = 125 °C		45.7		
			T_{vj} = 175 °C		43.8		
Rise time (inductive load)	t_r	I_D = 75 A, R_{Gon} = 10 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V, t_{dead} = 1000 ns, 0.1 I_D to 0.9 I_D	T_{vj} = 25 °C		24.5		ns
			T_{vj} = 125 °C		22.1		
			T_{vj} = 175 °C		21.5		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time (inductive load)	$t_{d\,off}$	I_D = 75 A, R_{Goff} = 2.7 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V, 0.9 V_{GS} to 0.9 I_D	T_{vj} = 25 °C		63		ns
			T_{vj} = 125 °C		71.4		
			T_{vj} = 175 °C		76.4		
Fall time (inductive load)	t_f	I_D = 75 A, R_{Goff} = 2.7 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V, 0.9 I_D to 0.1 I_D	T_{vj} = 25 °C		28.7		ns
			T_{vj} = 125 °C		31		
			T_{vj} = 175 °C		32.5		
Turn-on energy loss per pulse	E_{on}	I_D = 75 A, V_{DD} = 800 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Gon} = 10 Ω, di/dt = 4.11 kA/µs (T_{vj} = 175 °C), t_{dead} = 1000 ns	T_{vj} = 25 °C		2.57		mJ
			T_{vj} = 125 °C		2.74		
			T_{vj} = 175 °C		2.94		
Turn-on energy loss per pulse, optimized	$E_{on,o}$	I_D = 75 A, V_{DD} = 800 V, L_σ = 15 nH, V_{GS} = -3/18 V, $R_{Gon,o}$ = 1 Ω, di/dt = 10.6 kA/µs (T_{vj} = 175 °C), t_{dead} = 100 ns	T_{vj} = 25 °C		1.01		mJ
			T_{vj} = 125 °C		1.11		
			T_{vj} = 175 °C		1.27		
Turn-off energy loss per pulse	E_{off}	I_D = 75 A, V_{DD} = 800 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Goff} = 2.7 Ω, dv/dt = 28.2 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.8		mJ
			T_{vj} = 125 °C		0.86		
			T_{vj} = 175 °C		0.91		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material			0.62		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C
Temperature under overload switching conditions	$T_{vj\,over}$	Overload, cumulative max. 100 h				200	°C

***Note**: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2025-02 must be considered to ensure sound operation of the device over the planned lifetime.*

3 Body diode (MOSFET, T1 / T2)

Table 6 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	T_{vj} = 175 °C, V_{GS} = -3 V	T_H = 25 °C	55	A

Table 7 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 75 A, V_{GS}=-3 V	T_{vj} = 25 °C		4.35	5.35	V
			T_{vj} = 125 °C		4.05		
			T_{vj} = 175 °C		3.9		
Peak reverse recovery current	I_{rrm}	I_{SD} = 75 A, di_s/dt = 4.11 kA/µs, V_{DD} = 800 V, V_{GS} = -3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		35.2		A
			T_{vj} = 125 °C		50		
			T_{vj} = 175 °C		61.5		
Recovered charge	Q_{rr}	I_{SD} = 75 A, di_s/dt = 4.11 kA/µs, V_{DD} = 800 V, V_{GS} = -3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		0.51		µC
			T_{vj} = 125 °C		1.12		
			T_{vj} = 175 °C		1.59		
Reverse recovery energy	E_{rec}	I_{SD} = 75 A, di_s/dt = 4.11 kA/µs (T_{vj} = 175 °C), V_{DD} = 800 V, V_{GS} = -3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		0.13		mJ
			T_{vj} = 125 °C		0.34		
			T_{vj} = 175 °C		0.5		
Reverse recovery energy, optimized	$E_{rec,o}$	I_{SD} = 75 A, di_s/dt = 10.6 kA/µs (T_{vj} = 175 °C), V_{DD} = 800 V, V_{GS} = -3 V, t_{dead} = 100 ns	T_{vj} = 25 °C		0.89		mJ
			T_{vj} = 125 °C		1.73		
			T_{vj} = 175 °C		2.6		

4 MOSFET, T3 / T4

Table 8 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage	V_{DSS}		T_{vj} = 25 °C	1200	V
Implemented drain current	I_{DN}			75	A
Continuous DC drain current	I_{DDC}	T_{vj} = 175 °C, V_{GS} = 18 V	T_H = 25 °C	85	A
Repetitive peak drain current	I_{DRM}	verified by design, t_p limited by T_{vjmax}		150	A
Gate-source voltage, max. transient voltage	V_{GS}	D < 0.01		-10/25	V
Gate-source voltage, max. static voltage	V_{GS}			-7/20	V

Table 9 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
On-state gate voltage	$V_{GS(on)}$		15...18	V
Off-state gate voltage	$V_{GS(off)}$		-5...0	V

Table 10 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-resistance	$R_{DS(on)}$	I_D = 75 A	V_{GS} = 18 V, T_{vj} = 25 °C		8.3		mΩ
			V_{GS} = 18 V, T_{vj} = 125 °C		13		
			V_{GS} = 18 V, T_{vj} = 175 °C		16.8		
			V_{GS} = 15 V, T_{vj} = 25 °C		10		
Gate threshold voltage	$V_{GS(th)}$	I_D = 33 mA, V_{DS} = V_{GS}, T_{vj} = 25 °C, (tested after 1ms pulse at V_{GS} = +20 V), T_{vj} = 25 °C		3.45	4.3	5.15	V
Total gate charge	Q_G	V_{DD} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			0.237		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			3.5		Ω
Input capacitance	C_{ISS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		7.21		nF
Output capacitance	C_{OSS}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.293		nF
Reverse transfer capacitance	C_{rss}	f = 100 kHz, V_{DS} = 800 V, V_{GS} = 0 V	T_{vj} = 25 °C		0.02		nF
C_{OSS} stored energy	E_{OSS}	V_{DS} = 800 V, V_{GS} = -3/18 V, T_{vj} = 25 °C			121		µJ
Drain-source leakage current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = -3 V	T_{vj} = 25 °C		0.3	296	µA
Gate-source leakage current	I_{GSS}	V_{DS} = 0 V, T_{vj} = 25 °C	V_{GS} = 20 V			400	nA
Turn-on delay time (inductive load)	$t_{d\,on}$	I_D = 75 A, R_{Gon} = 5.6 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V, t_{dead} = 1000 ns, 0.1 V_{GS} to 0.1 I_D	T_{vj} = 25 °C		46		ns
			T_{vj} = 125 °C		42.9		
			T_{vj} = 175 °C		41.1		
Rise time (inductive load)	t_r	I_D = 75 A, R_{Gon} = 5.6 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V, t_{dead} = 1000 ns, 0.1 I_D to 0.9 I_D	T_{vj} = 25 °C		19.9		ns
			T_{vj} = 125 °C		17.8		
			T_{vj} = 175 °C		17.1		
Turn-off delay time (inductive load)	$t_{d\,off}$	I_D = 75 A, R_{Goff} = 2.7 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V, 0.9 V_{GS} to 0.9 I_D	T_{vj} = 25 °C		64.1		ns
			T_{vj} = 125 °C		73.5		
			T_{vj} = 175 °C		79.2		
Fall time (inductive load)	t_f	I_D = 75 A, R_{Goff} = 2.7 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V, 0.9 I_D to 0.1 I_D	T_{vj} = 25 °C		30.7		ns
			T_{vj} = 125 °C		31.9		
			T_{vj} = 175 °C		32.3		

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-on energy loss per pulse	E_{on}	I_D = 75 A, V_{DD} = 800 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Gon} = 5.6 Ω, di/dt = 4.95 kA/µs (T_{vj} = 175 °C), t_{dead} = 1000 ns	T_{vj} = 25 °C		2.02		mJ
			T_{vj} = 125 °C		2.19		
			T_{vj} = 175 °C		2.43		
Turn-on energy loss per pulse, optimized	$E_{on,o}$	I_D = 75 A, V_{DD} = 800 V, L_σ = 15 nH, V_{GS} = -3/18 V, $R_{Gon,o}$ = 0 Ω, di/dt = 11.1 kA/µs (T_{vj} = 175 °C), t_{dead} = 100 ns	T_{vj} = 25 °C		0.81		mJ
			T_{vj} = 125 °C		0.85		
			T_{vj} = 175 °C		0.99		
Turn-off energy loss per pulse	E_{off}	I_D = 75 A, V_{DD} = 800 V, L_σ = 15 nH, V_{GS} = -3/18 V, R_{Goff} = 2.7 Ω, dv/dt = 25.8 kV/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.83		mJ
			T_{vj} = 125 °C		0.92		
			T_{vj} = 175 °C		0.98		
Thermal resistance, junction to heat sink	R_{thJH}	per MOSFET, Valid with IFX pre-applied Thermal Interface Material			0.78		K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C
Temperature under overload switching conditions	$T_{vj\,over}$	Overload, cumulative max. 100 h				200	°C

***Note**: The selection of positive and negative gate-source voltages impacts losses and the long-term behavior of the MOSFET and body diode. The design guidelines described in Application Notes AN 2018-09 and AN 2025-02 must be considered to ensure sound operation of the device over the planned lifetime.*

5 Body diode (MOSFET, T3 / T4)

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
DC body diode forward current	I_{SD}	T_{vj} = 175 °C, V_{GS} = -3 V	T_H = 25 °C	45	A

Table 12 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_{SD}	I_{SD} = 75 A, V_{GS}=-3 V	T_{vj} = 25 °C		4.35	5.35	V
			T_{vj} = 125 °C		4.05		
			T_{vj} = 175 °C		3.9		

(table continues...)

Table 12 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Peak reverse recovery current	I_{rrm}	I_{SD} = 75 A, di_s/dt = 4.95 kA/µs, V_{DD} = 800 V, V_{GS} = -3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		40.7		A
			T_{vj} = 125 °C		58.1		
			T_{vj} = 175 °C		70.5		
Recovered charge	Q_{rr}	I_{SD} = 75 A, di_s/dt = 4.95 kA/µs, V_{DD} = 800 V, V_{GS} = -3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		0.55		µC
			T_{vj} = 125 °C		1.18		
			T_{vj} = 175 °C		1.61		
Reverse recovery energy	E_{rec}	I_{SD} = 75 A, di_s/dt = 4.95 kA/µs (T_{vj} = 175 °C), V_{DD} = 800 V, V_{GS} = -3 V, t_{dead} = 1000 ns	T_{vj} = 25 °C		0.14		mJ
			T_{vj} = 125 °C		0.37		
			T_{vj} = 175 °C		0.49		
Reverse recovery energy, optimized	$E_{rec,o}$	I_{SD} = 75 A, di_s/dt = 11.1 kA/µs (T_{vj} = 175 °C), V_{DD} = 800 V, V_{GS} = -3 V, t_{dead} = 100 ns	T_{vj} = 25 °C		0.88		mJ
			T_{vj} = 125 °C		1.47		
			T_{vj} = 175 °C		1.92		

6 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2-1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2-1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2-1/(298{,}15\ K))]$		3433		K

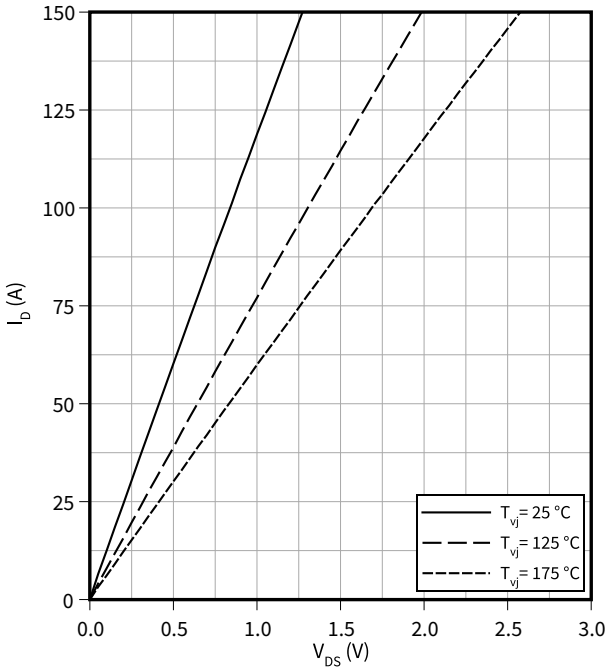
***Note**: For an analytical description of the NTC characteristics please refer to AN2009-10, chapter 4*

7 Characteristics diagrams

Output characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

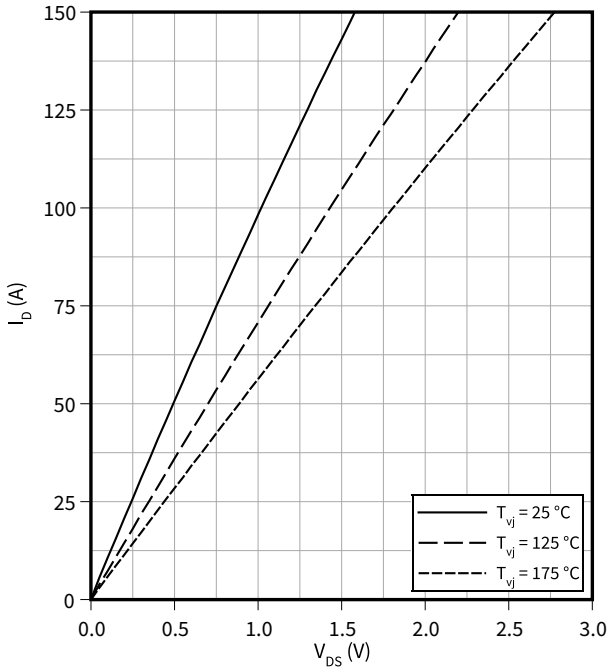
$V_{GS} = 18$ V



Output characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{DS})$

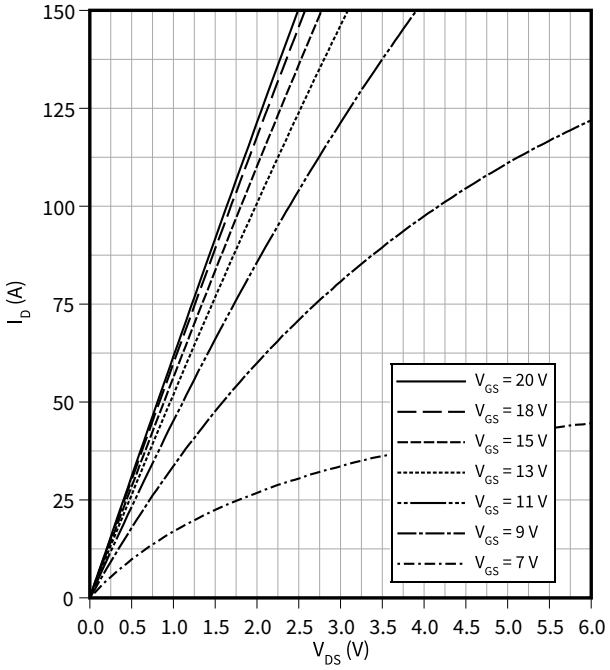
$V_{GS} = 15$ V



Output characteristic field (typical), MOSFET, T1 / T2

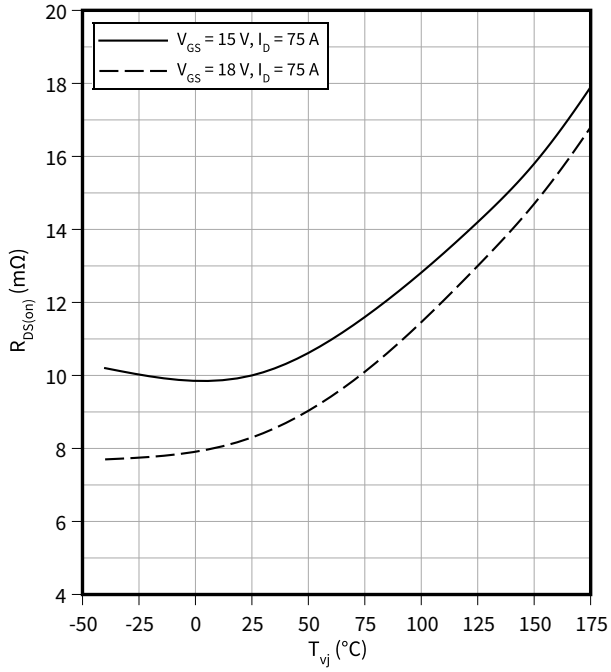
$I_D = f(V_{DS})$

$T_{vj} = 175$ °C



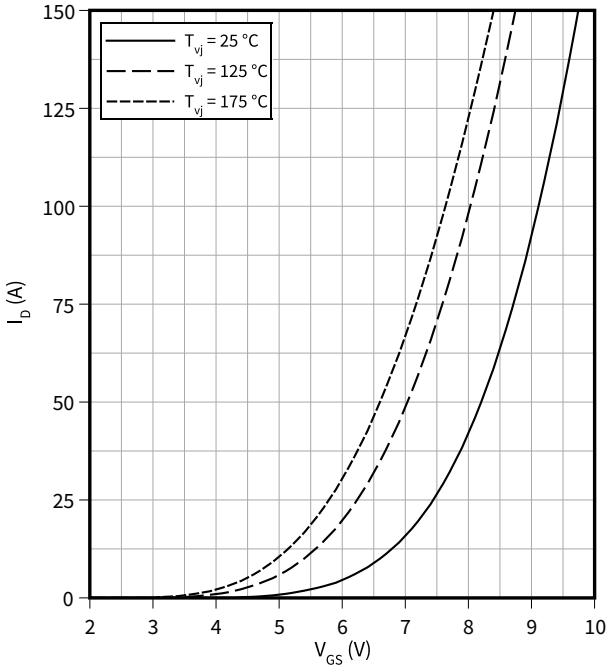
Drain source on-resistance (typical), MOSFET, T1 / T2

$R_{DS(on)} = f(T_{vj})$



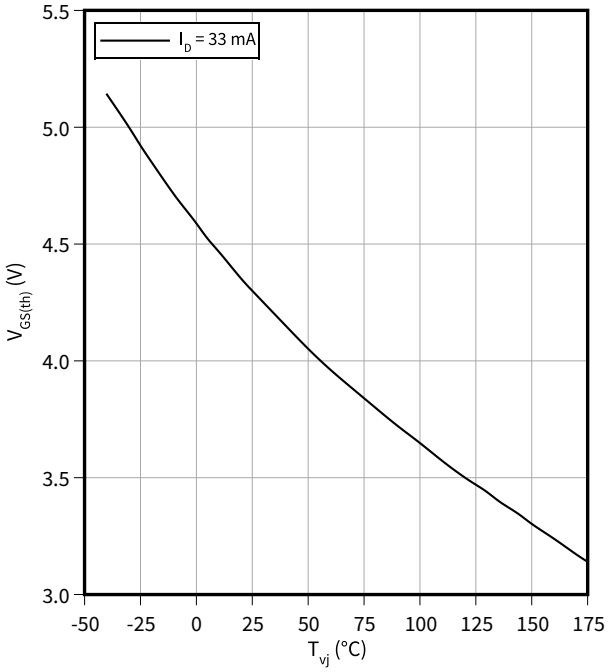
Transfer characteristic (typical), MOSFET, T1 / T2

$I_D = f(V_{GS})$
$V_{DS} = 20$ V



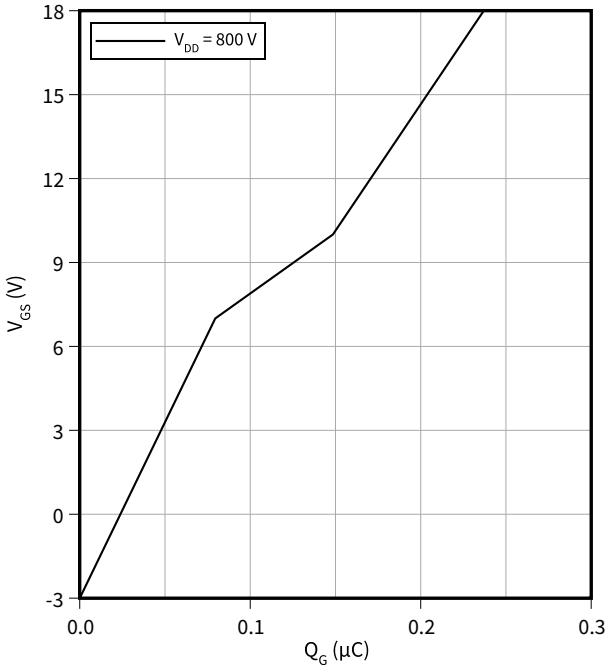
Gate-source threshold voltage (typical), MOSFET, T1 / T2

$V_{GS(th)} = f(T_{vj})$
$V_{GS} = V_{DS}$



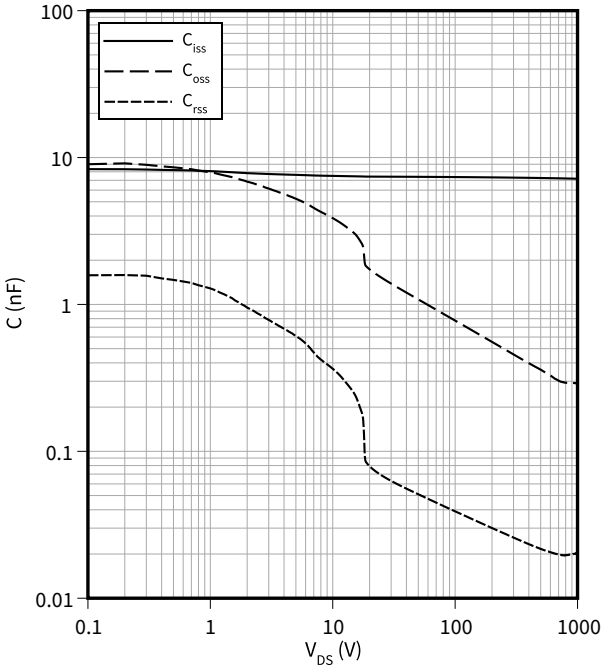
Gate charge characteristic (typical), MOSFET, T1 / T2

$V_{GS} = f(Q_G)$
$I_D = 75$ A, $T_{vj} = 25$ °C



Capacity characteristic (typical), MOSFET, T1 / T2

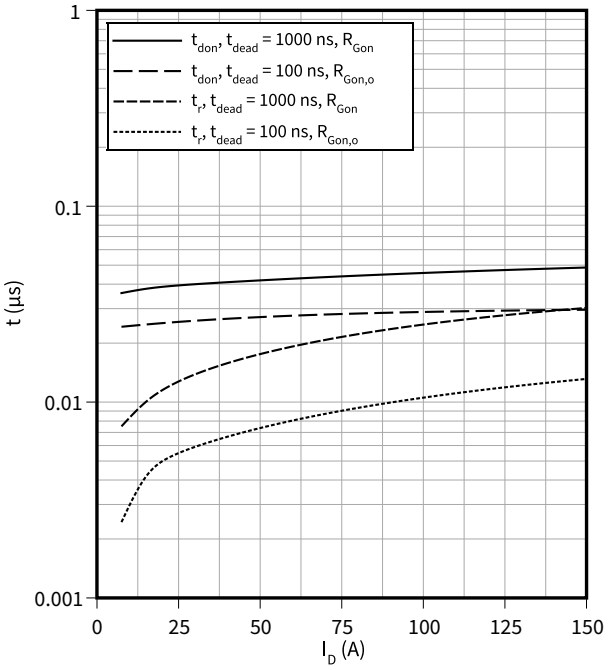
$C = f(V_{DS})$
$f = 100$ kHz, $T_{vj} = 25$ °C, $V_{GS} = 0$ V



Switching times (typical), MOSFET, T1 / T2

$t = f(I_D)$

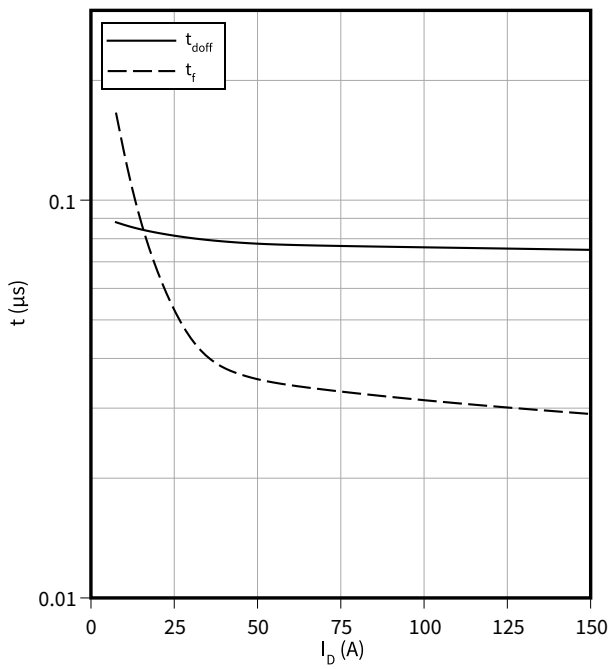
V_{DD} = 800 V, R_{Gon} = 10 Ω, $R_{Gon,o}$ = 1 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET, T1 / T2

$t = f(I_D)$

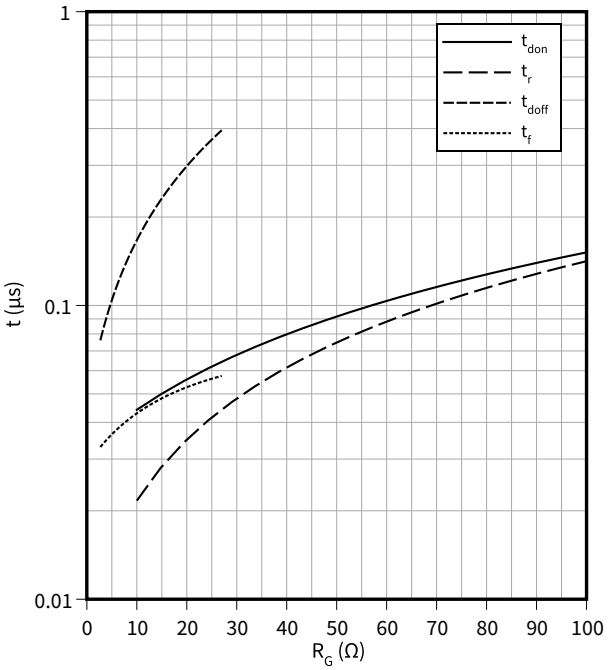
R_{Goff} = 2.7 Ω, V_{DD} = 800 V, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET, T1 / T2

$t = f(R_G)$

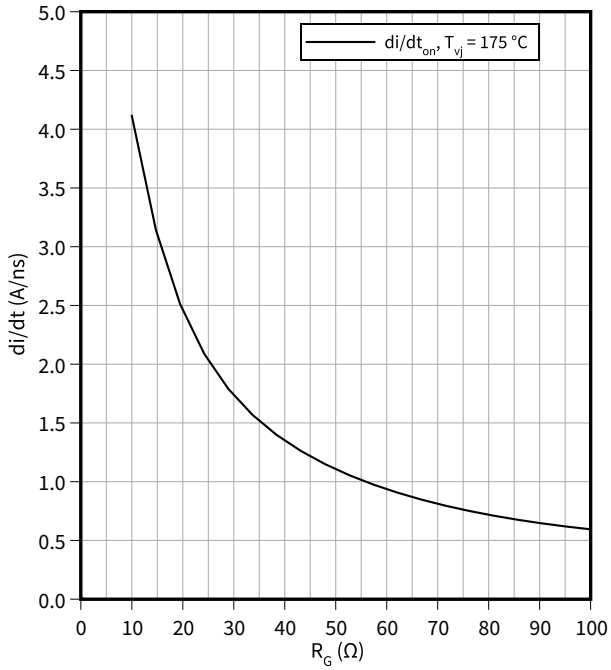
V_{DD} = 800 V, t_{dead} = 1000 ns, I_D = 75 A, T_{vj} = 175 °C, V_{GS} = -3/18 V



Current slope (typical), MOSFET, T1 / T2

$di/dt = f(R_G)$

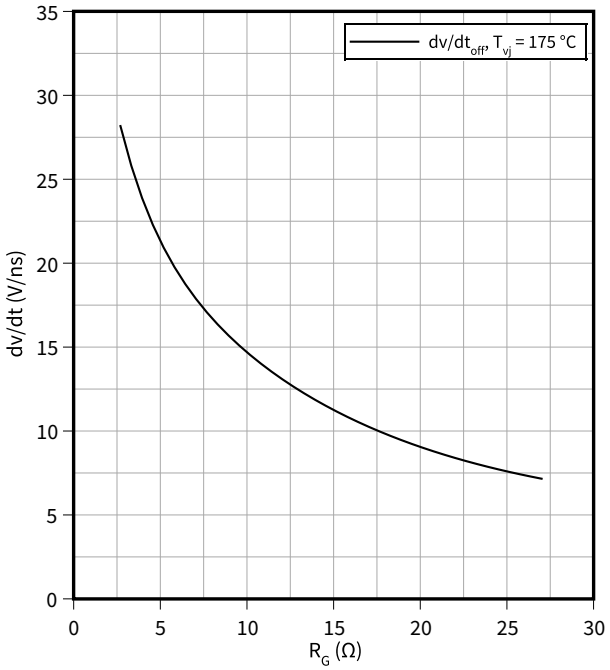
V_{DD} = 800 V, t_{dead} = 1000 ns, I_D = 75 A, V_{GS} = -3/18 V



Voltage slope (typical), MOSFET, T1 / T2

$dv/dt = f(R_G)$

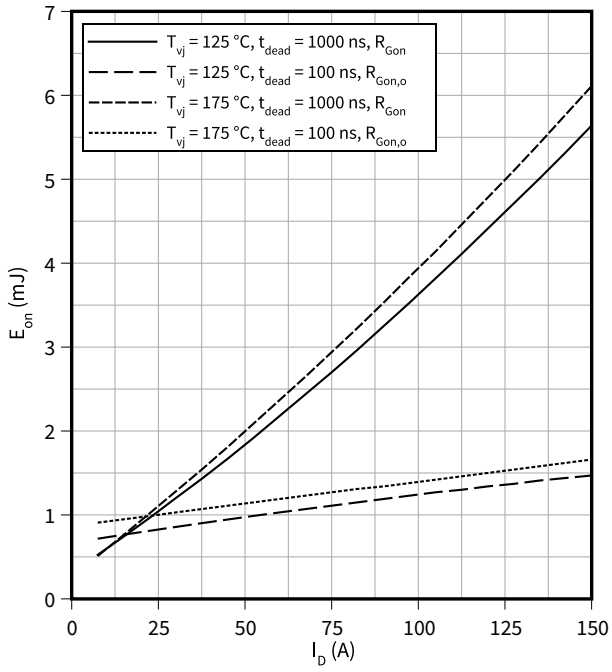
V_{DD} = 800 V, I_D = 75 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(I_D)$

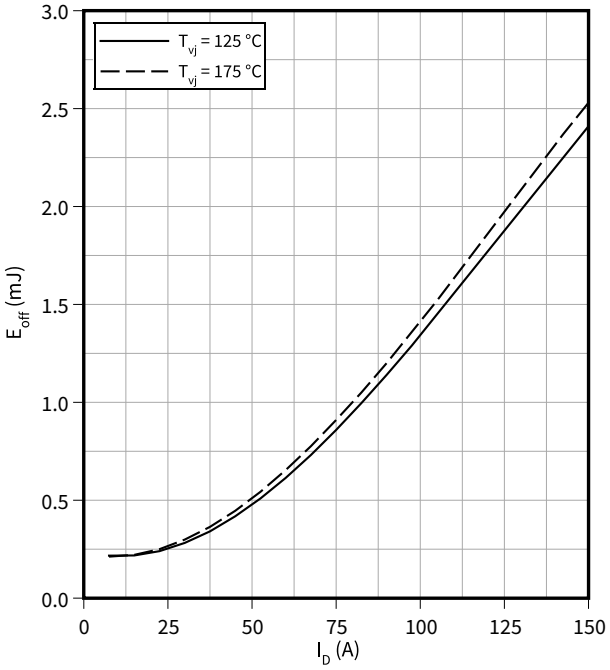
V_{DD} = 800 V, R_{Gon} = 10 Ω, $R_{Gon,o}$ = 1 Ω, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T1 / T2

$E_{off} = f(I_D)$

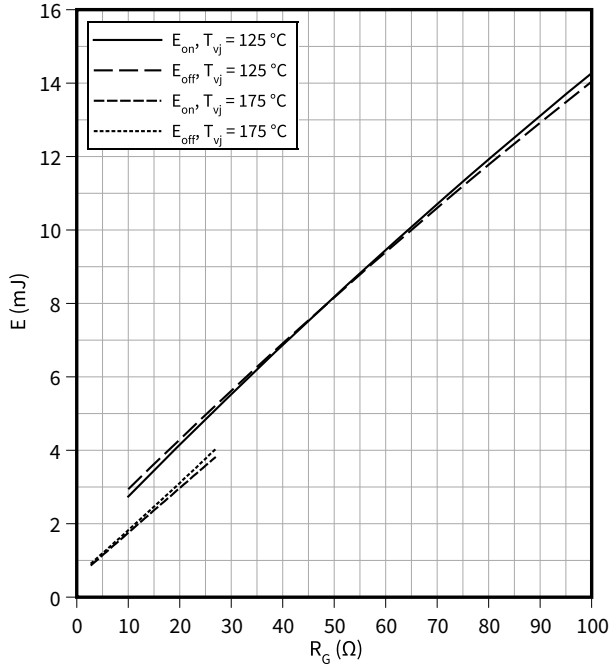
R_{Goff} = 2.7 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T1 / T2

$E = f(R_G)$

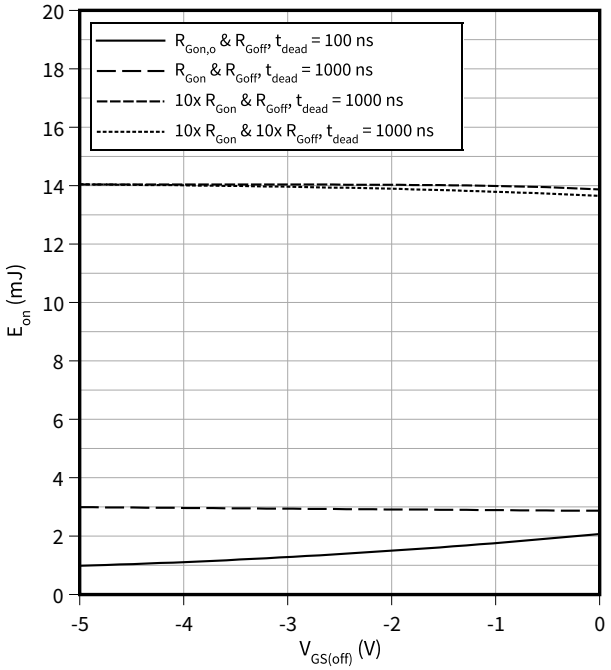
V_{DD} = 800 V, t_{dead} = 1000 ns, I_D = 75 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(V_{GS(off)})$

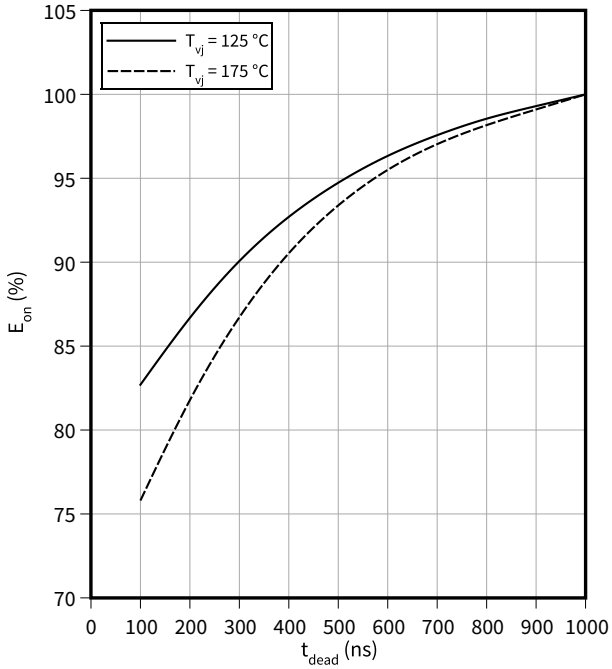
R_{Goff} = 2.7 Ω, V_{DD} = 800 V, R_{Gon} = 10 Ω, $V_{GS(on)}$ = 18 V, I_D = 75 A, $R_{Gon,o}$ = 1 Ω, T_{vj} = 175 °C



Switching losses (typical), MOSFET, T1 / T2

$E_{on} = f(t_{dead})$

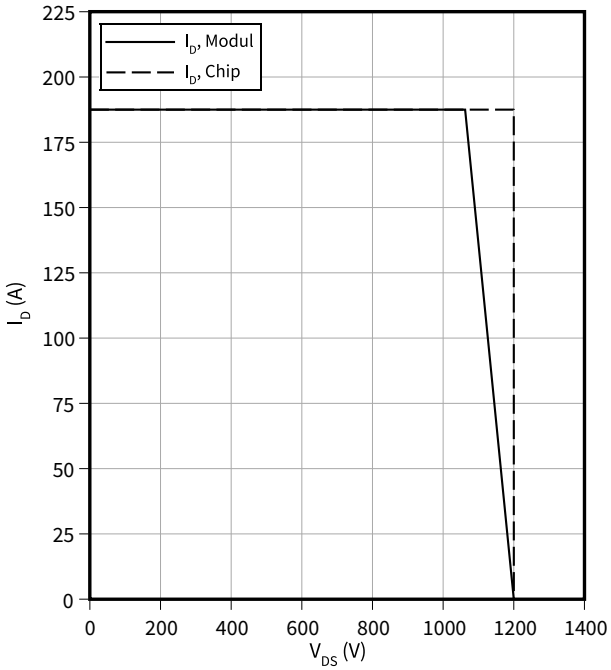
R_{Gon} = 10 Ω, I_D = 75 A, V_{DD} = 800 V, V_{GS} = -3/18 V



Reverse bias safe operating area (RBSOA), MOSFET, T1 / T2

$I_D = f(V_{DS})$

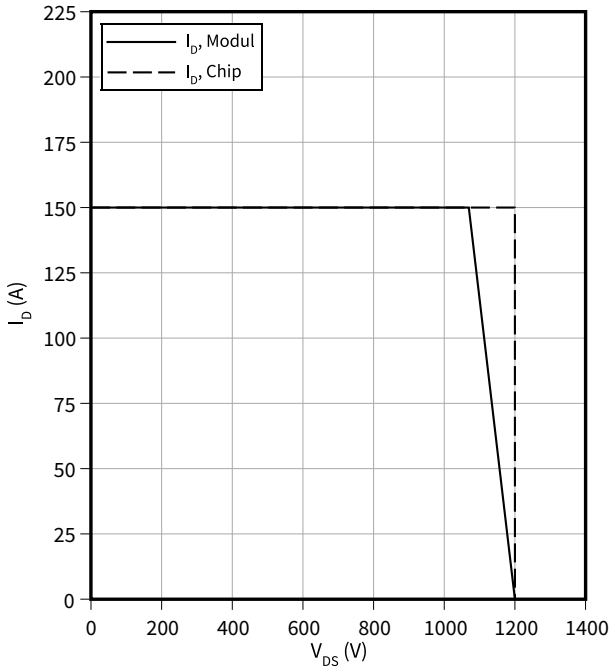
R_{Goff} = 3.3 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Reverse bias safe operating area (RBSOA), MOSFET, T1 / T2

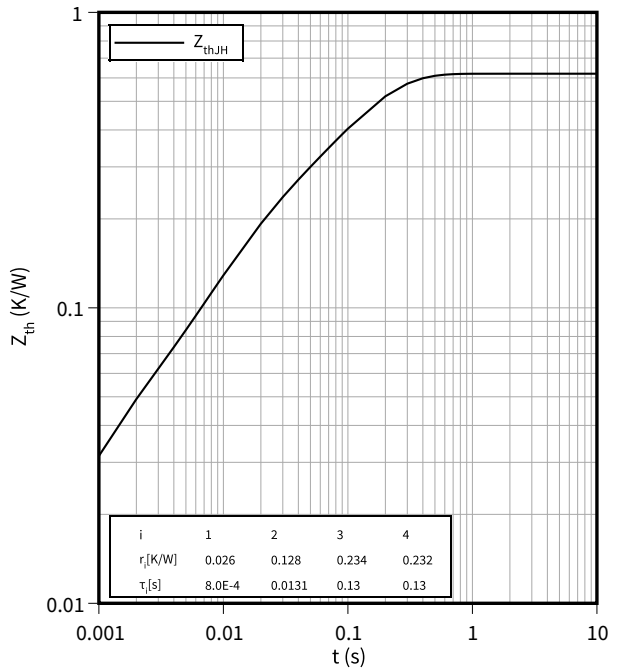
$I_D = f(V_{DS})$

R_{Goff} = 2.7 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Transient thermal impedance, MOSFET, T1 / T2

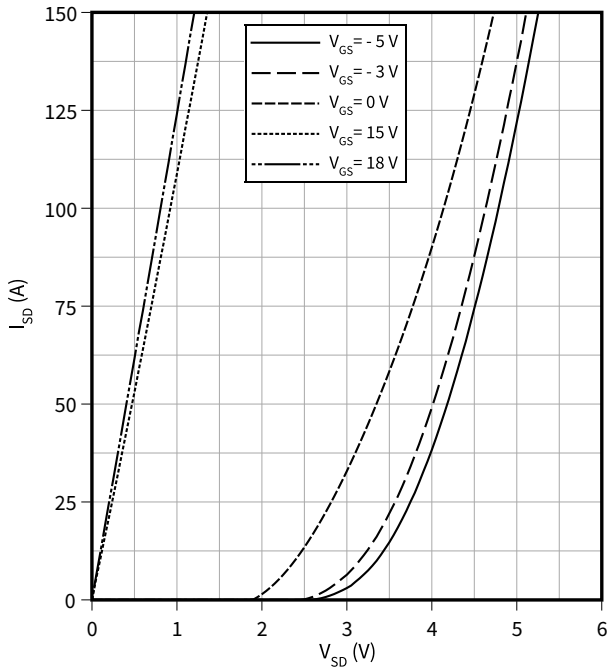
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET, T1 / T2

$I_{SD} = f(V_{SD})$

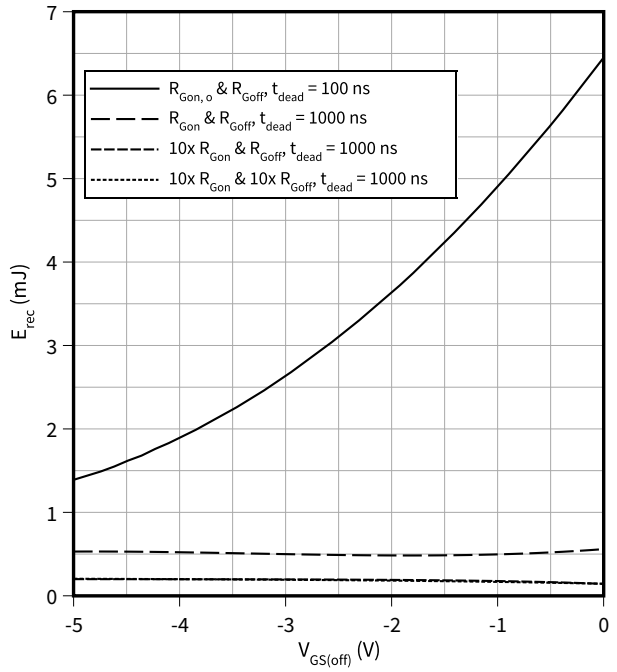
$T_{vj} = 25\ °C$



Switching losses body diode (typical), MOSFET, T1 / T2

$E_{rec} = f(V_{GS(off)})$

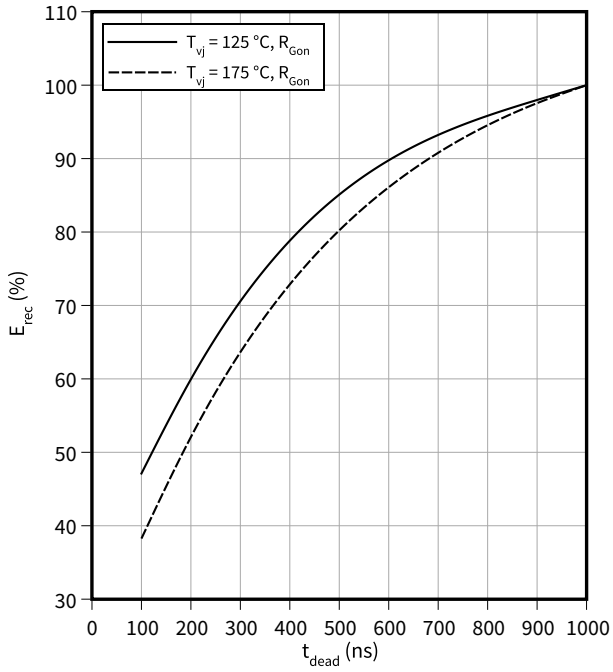
$R_{Goff} = 2.7\ \Omega$, $R_{Gon} = 10\ \Omega$, $V_{GS(on)} = 18\ V$, $I_{SD} = 75\ A$, $R_{Gon,o} = 1\ \Omega$, $V_{DD} = 800\ V$, $T_{vj} = 175\ °C$



Switching losses body diode (typical), MOSFET, T1 / T2

$E_{rec} = f(t_{dead})$

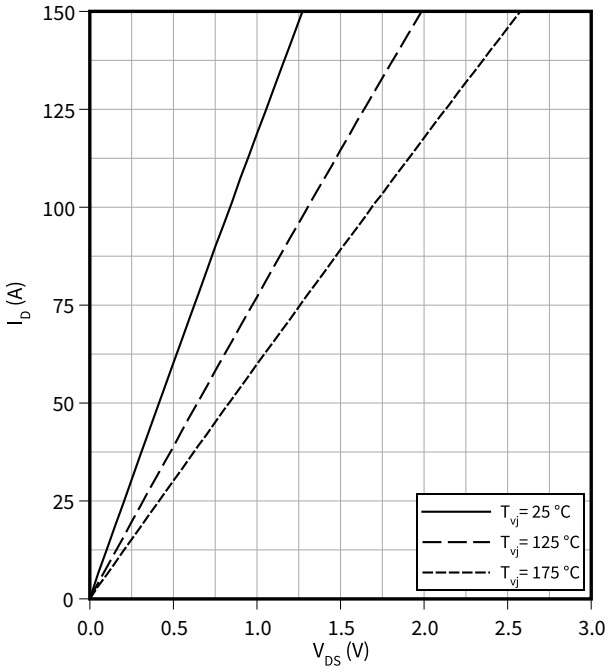
$R_{Gon} = 10\ \Omega$, $I_D = 75\ A$, $V_{DD} = 800\ V$, $V_{GS} = -3/18\ V$



Output characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{DS})$

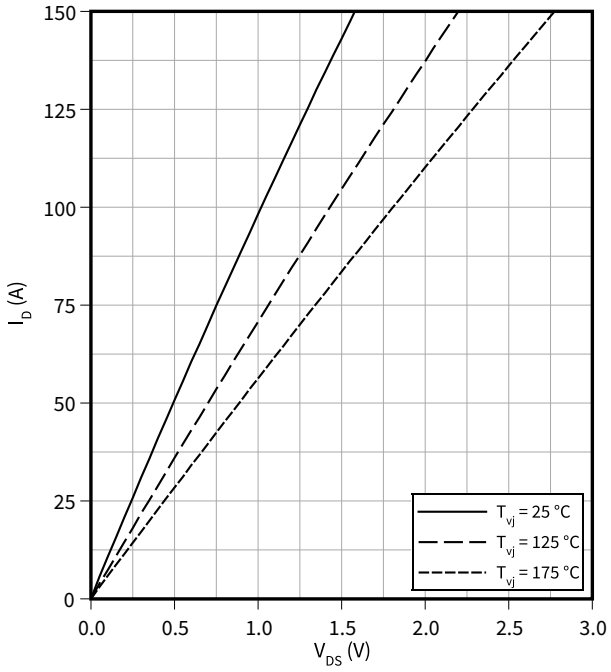
$V_{GS} = 18$ V



Output characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{DS})$

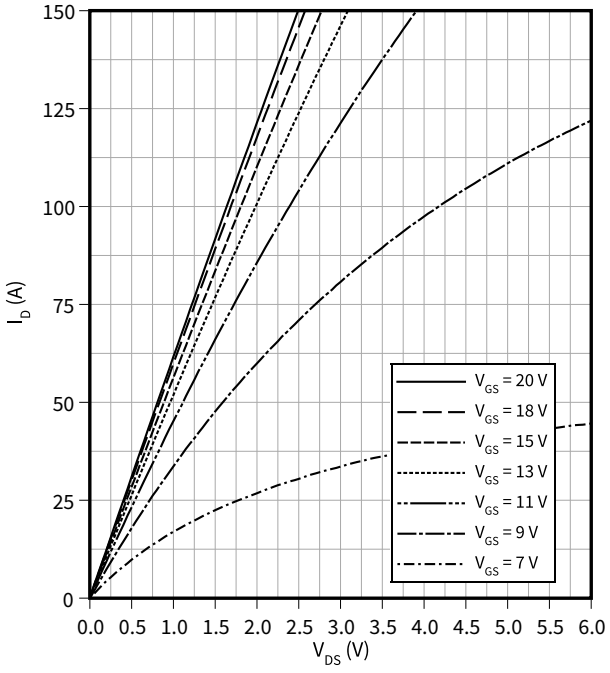
$V_{GS} = 15$ V



Output characteristic field (typical), MOSFET, T3 / T4

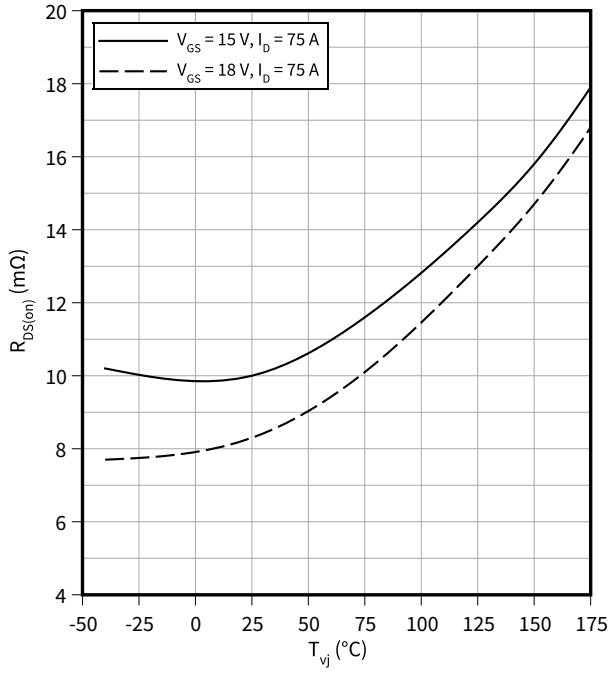
$I_D = f(V_{DS})$

$T_{vj} = 175$ °C



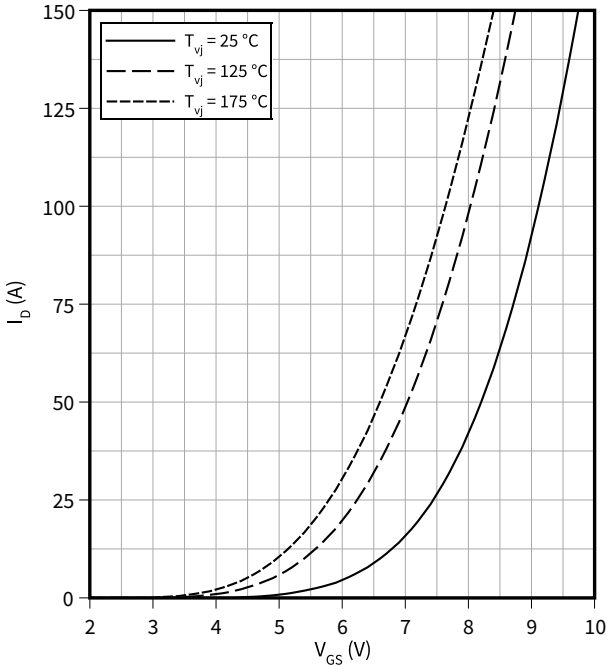
Drain source on-resistance (typical), MOSFET, T3 / T4

$R_{DS(on)} = f(T_{vj})$



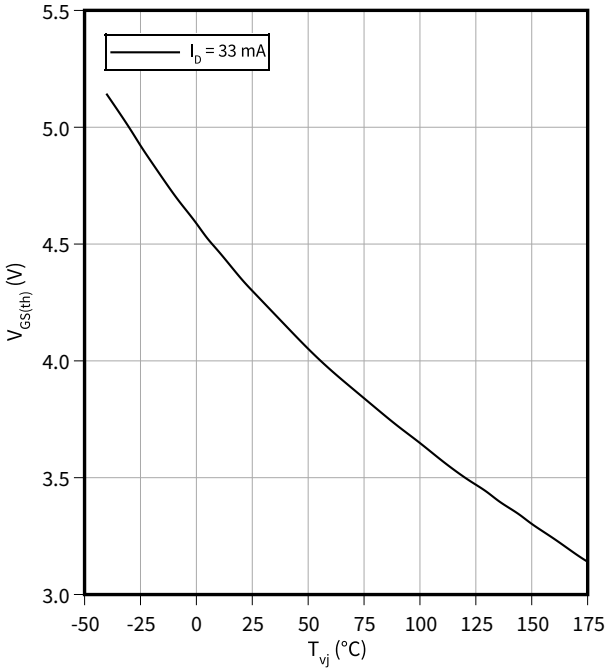
Transfer characteristic (typical), MOSFET, T3 / T4

$I_D = f(V_{GS})$
$V_{DS} = 20$ V



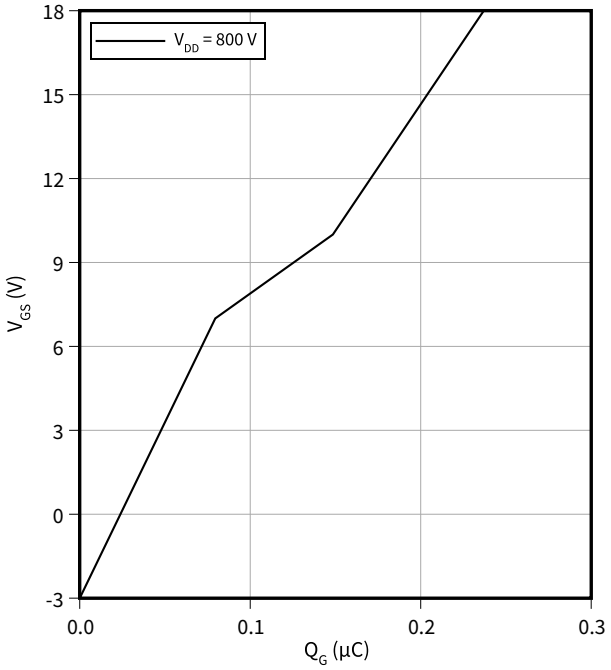
Gate-source threshold voltage (typical), MOSFET, T3 / T4

$V_{GS(th)} = f(T_{vj})$
$V_{GS} = V_{DS}$



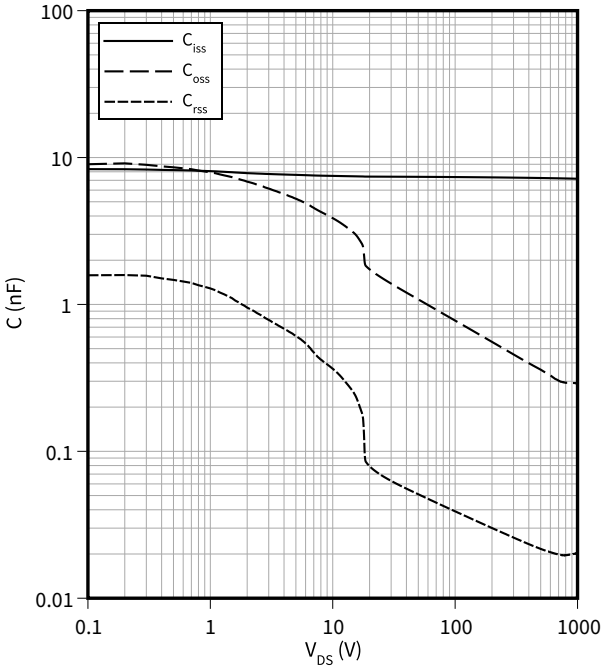
Gate charge characteristic (typical), MOSFET, T3 / T4

$V_{GS} = f(Q_G)$
$I_D = 75$ A, $T_{vj} = 25$ °C



Capacity characteristic (typical), MOSFET, T3 / T4

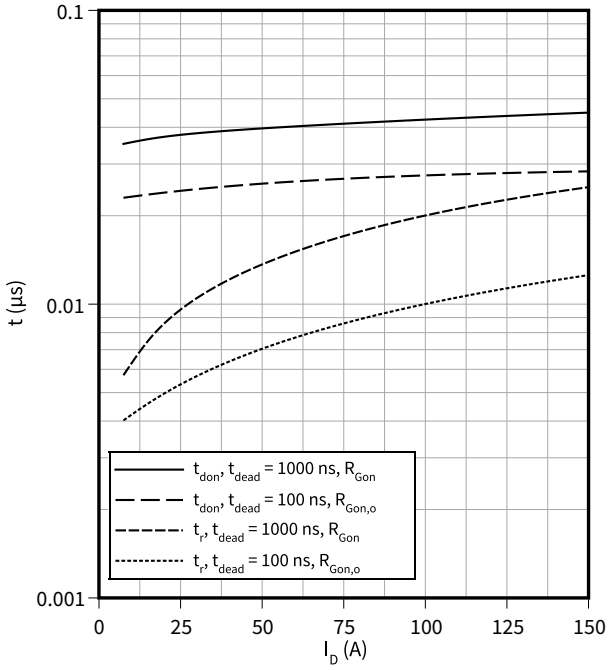
$C = f(V_{DS})$
$f = 100$ kHz, $T_{vj} = 25$ °C, $V_{GS} = 0$ V



Switching times (typical), MOSFET, T3 / T4

$t = f(I_D)$

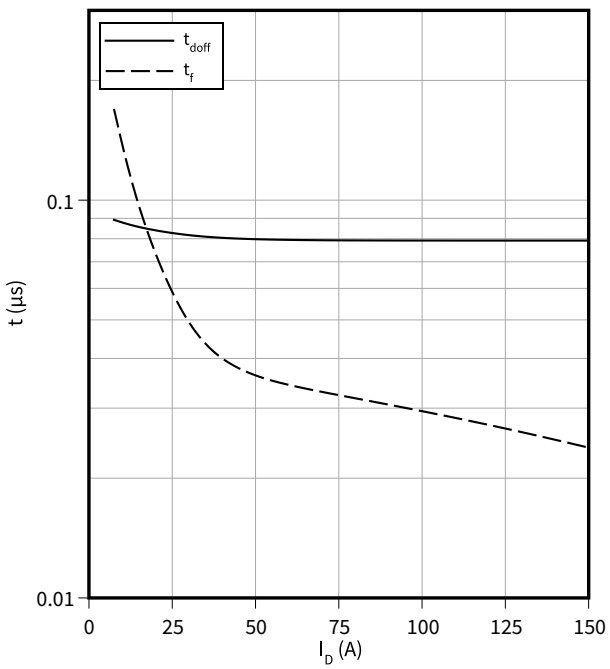
V_{DD} = 800 V, R_{Gon} = 5.6 Ω, $R_{Gon,o}$ = 0 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET, T3 / T4

$t = f(I_D)$

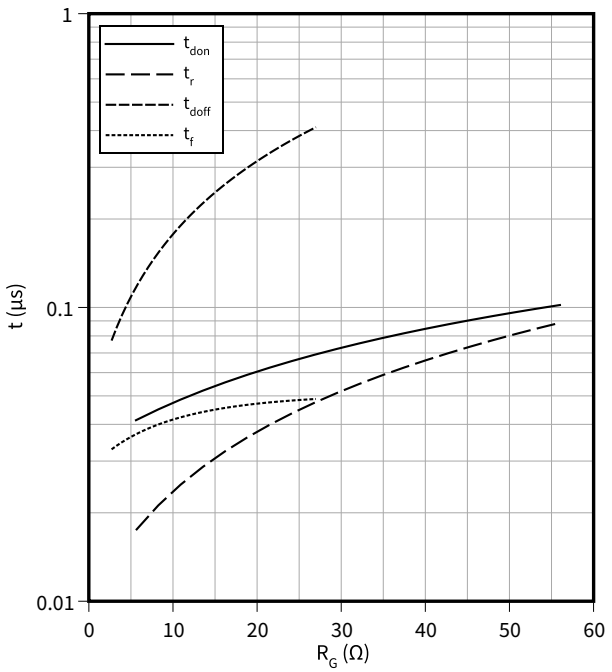
R_{Goff} = 2.7 Ω, V_{DD} = 800 V, T_{vj} = 175 °C, V_{GS} = -3/18 V



Switching times (typical), MOSFET, T3 / T4

$t = f(R_G)$

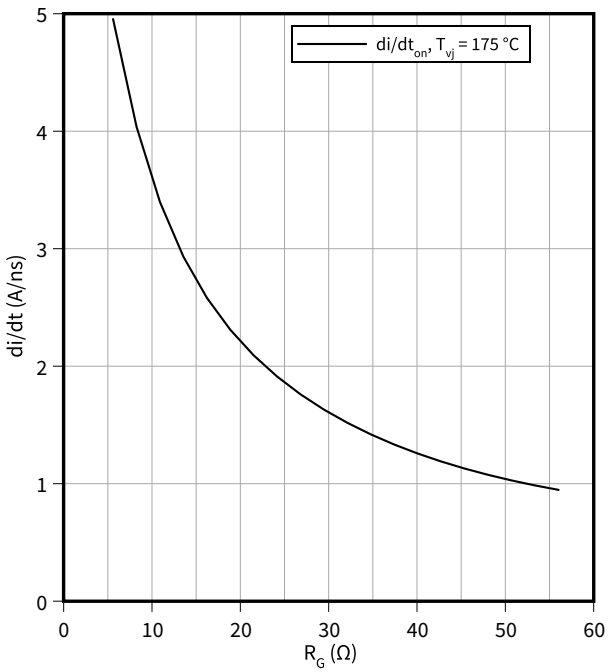
V_{DD} = 800 V, t_{dead} = 1000 ns, I_D = 75 A, T_{vj} = 175 °C, V_{GS} = -3/18 V



Current slope (typical), MOSFET, T3 / T4

$di/dt = f(R_G)$

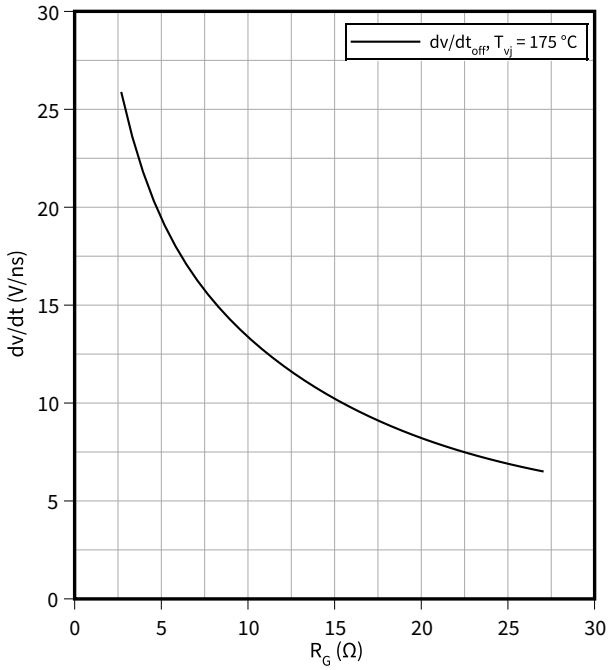
V_{DD} = 800 V, t_{dead} = 1000 ns, I_D = 75 A, V_{GS} = -3/18 V



Voltage slope (typical), MOSFET, T3 / T4

$dv/dt = f(R_G)$

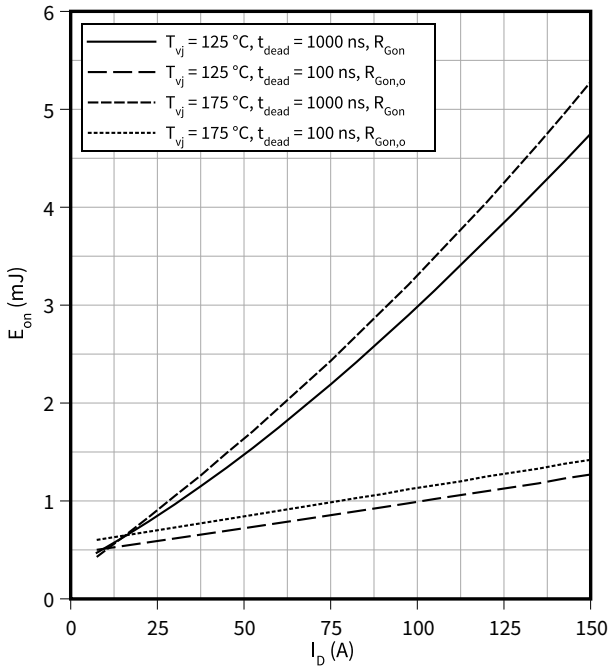
V_{DD} = 800 V, I_D = 75 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(I_D)$

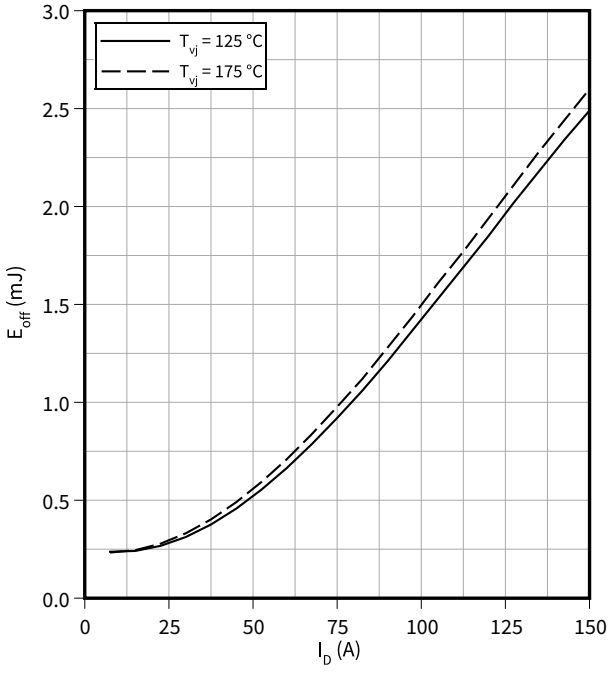
V_{DD} = 800 V, R_{Gon} = 5.6 Ω, $R_{Gon,o}$ = 0 Ω, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T3 / T4

$E_{off} = f(I_D)$

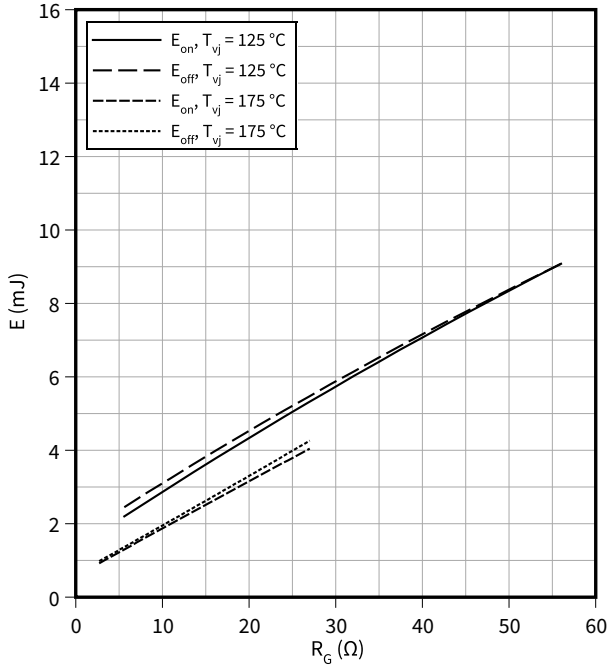
R_{Goff} = 2.7 Ω, V_{DD} = 800 V, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T3 / T4

$E = f(R_G)$

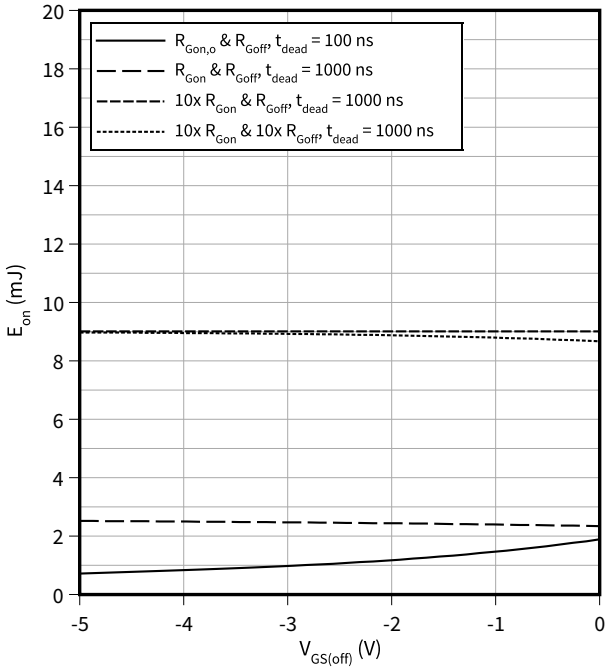
V_{DD} = 800 V, t_{dead} = 1000 ns, I_D = 75 A, V_{GS} = -3/18 V



Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(V_{GS(off)})$

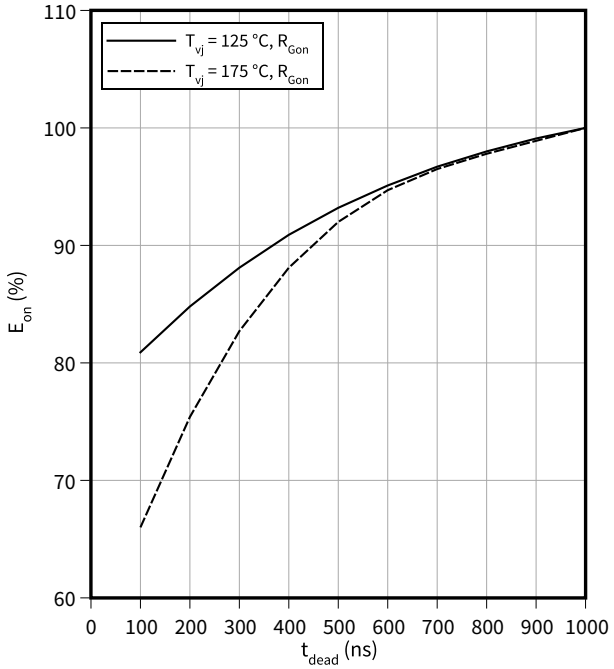
R_{Goff} = 2.7 Ω, V_{DD} = 800 V, R_{Gon} = 5.6 Ω, $V_{GS(on)}$ = 18 V, I_D = 75 A, $R_{Gon,o}$ = 0 Ω, T_{vj} = 175 °C



Switching losses (typical), MOSFET, T3 / T4

$E_{on} = f(t_{dead})$

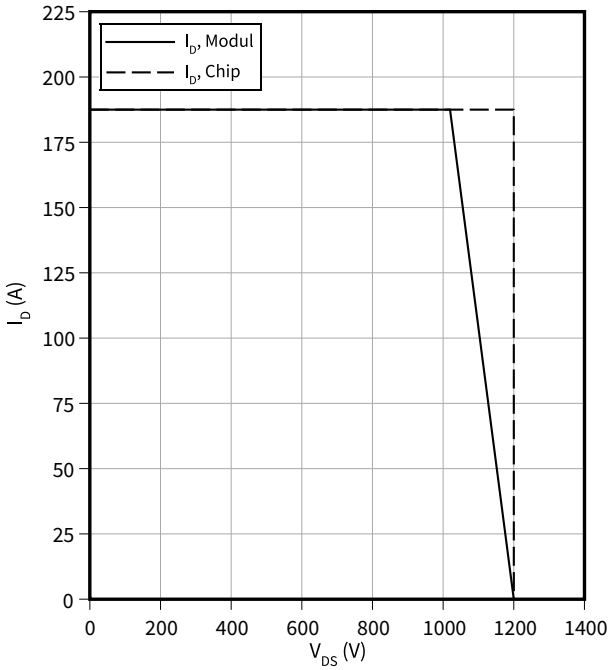
R_{Gon} = 5.6 Ω, I_D = 75 A, V_{DD} = 800 V, V_{GS} = -3/18 V



Reverse bias safe operating area (RBSOA), MOSFET, T3 / T4

$I_D = f(V_{DS})$

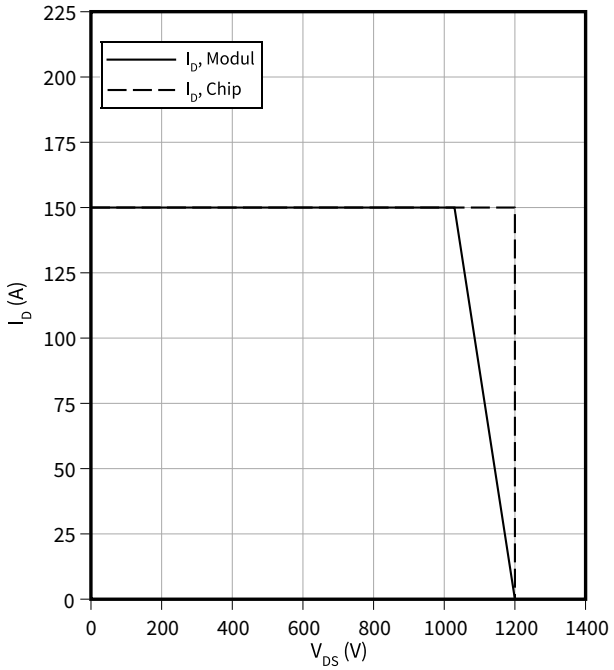
R_{Goff} = 3.6 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Reverse bias safe operating area (RBSOA), MOSFET, T3 / T4

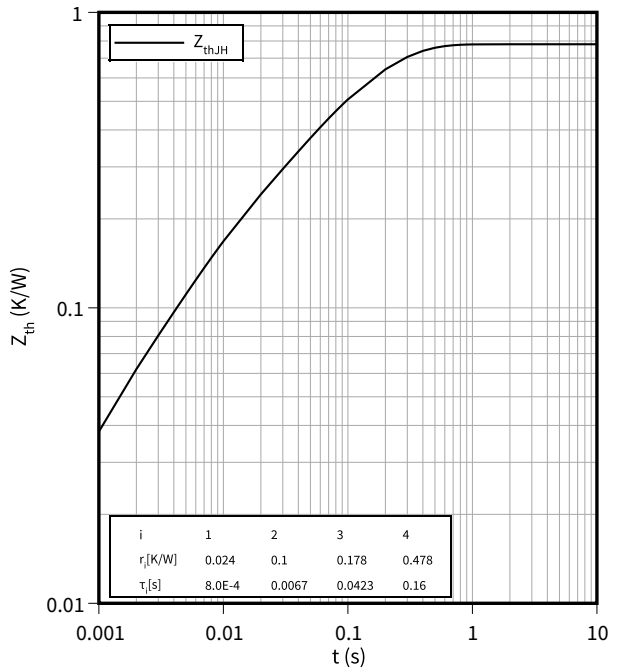
$I_D = f(V_{DS})$

R_{Goff} = 2.7 Ω, T_{vj} = 175 °C, V_{GS} = -3/18 V



Transient thermal impedance, MOSFET, T3 / T4

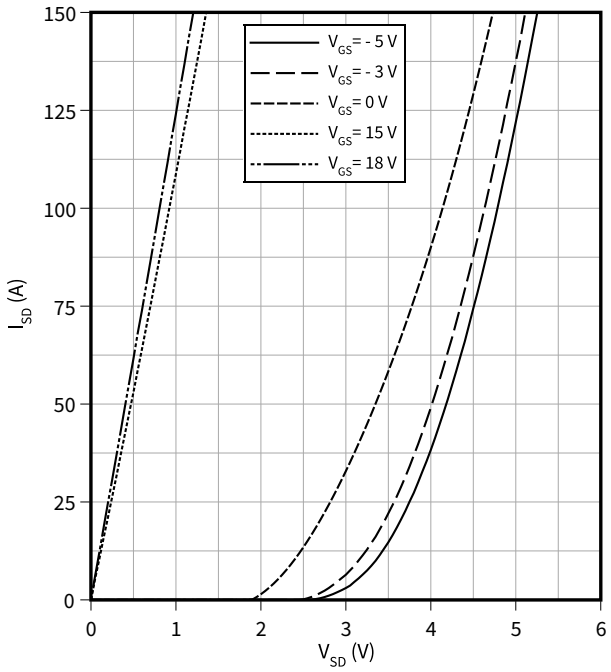
$Z_{th} = f(t)$



Forward characteristic body diode (typical), MOSFET, T3 / T4

$I_{SD} = f(V_{SD})$

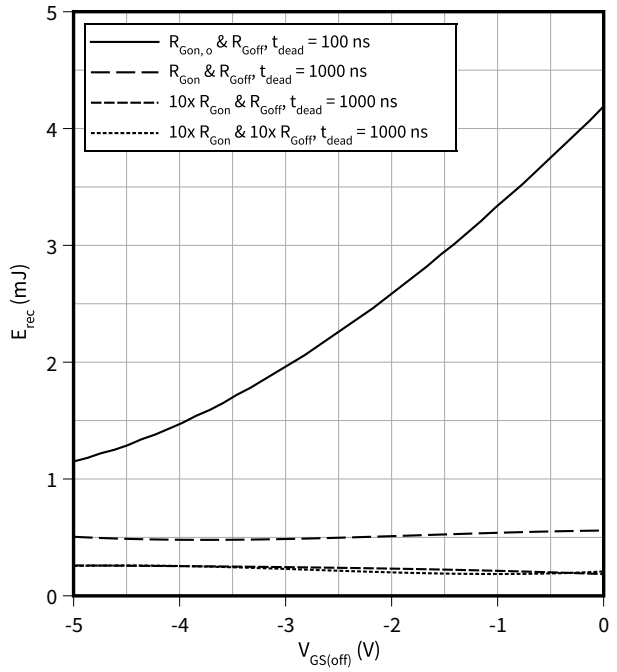
$T_{vj} = 25\ °C$



Switching losses body diode (typical), MOSFET, T3 / T4

$E_{rec} = f(V_{GS(off)})$

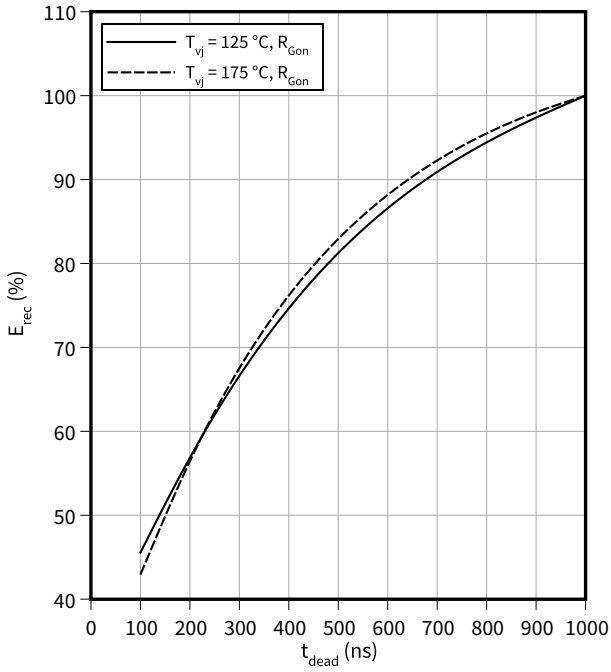
$R_{Goff} = 2.7\ \Omega$, $R_{Gon} = 5.6\ \Omega$, $V_{GS(on)} = 18\ V$, $I_{SD} = 75\ A$, $R_{Gon,o} = 0\ \Omega$, $V_{DD} = 800\ V$, $T_{vj} = 175\ °C$



Switching losses body diode (typical), MOSFET, T3 / T4

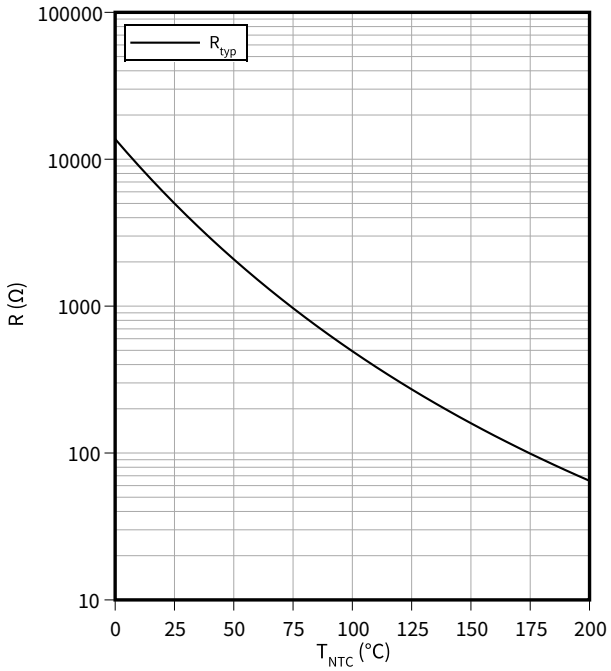
$E_{rec} = f(t_{dead})$

$R_{Gon} = 5.6\ \Omega$, $I_D = 75\ A$, $V_{DD} = 800\ V$, $V_{GS} = -3/18\ V$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



8 Circuit diagram

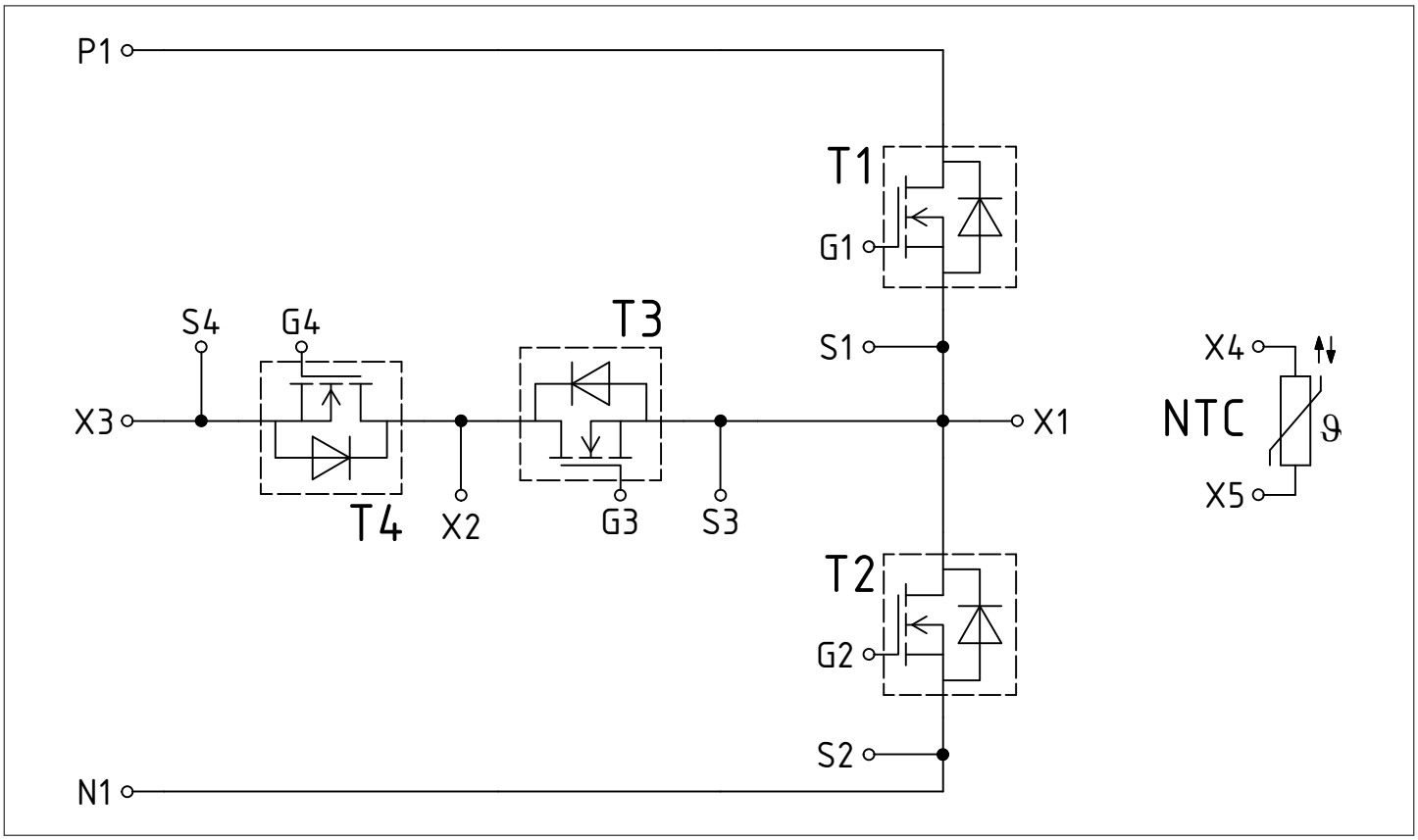


Figure 1

9 Package outlines

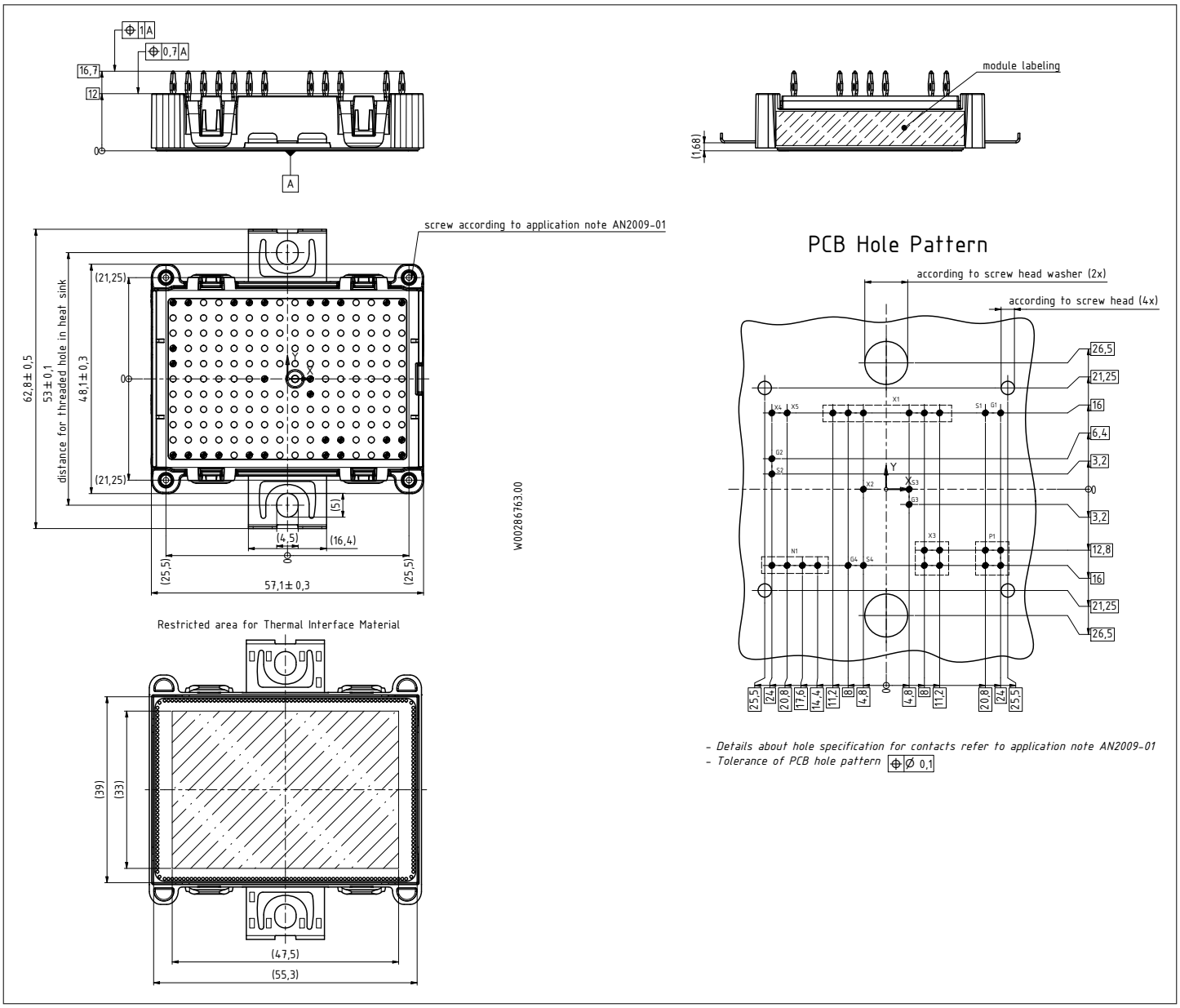


Figure 2

10 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2025-07-01	Preliminary datasheet

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